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(54) Title: PHOTORESIST REMOVAL

(57) Abstract: Disclosed herein is a composition and method for semiconductor processing. In one embodiment, a wet-cleaning composition for removal of photoresist is provided. The composition comprises a strong base; an oxidant; and a polar solvent. In another embodiment, a method for removing photoresist is provided. The method comprises the steps of applying a wet-cleaning composition comprising about 0.1 to about 30 weight percent strong base; about one to about 30 weight percent oxidant; about 20 to about 95 weight percent polar solvent; and removing the photoresist.

WO 2004/059700 A2